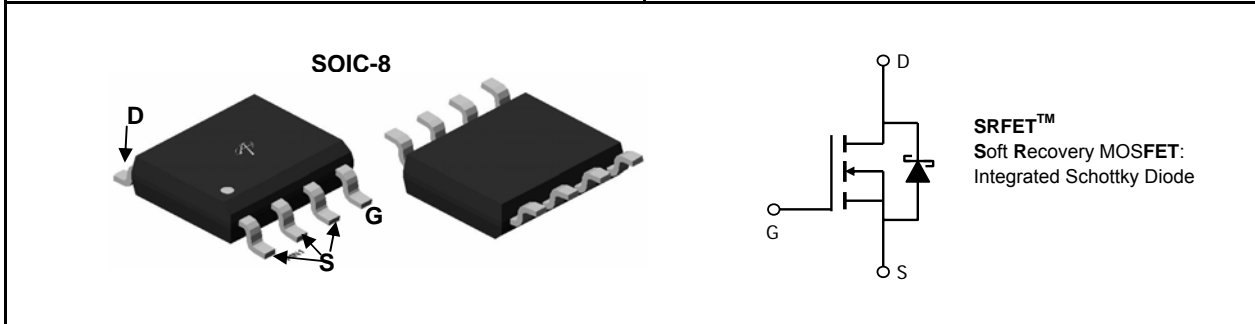


AO4728L
N-Channel Enhancement Mode Field Effect Transistor
SRFET™

General Description	Features
SRFET™ AO4728L uses advanced trench technology with a monolithically integrated Schottky diode to provide excellent $R_{DS(ON)}$, and low gate charge. This device is ideally suited for use as a low side switch in CPU core power conversion.	$V_{DS} (V) = 30V$ $I_D = 20A$ ($V_{GS} = 10V$) $R_{DS(ON)} < 4.3m\Omega$ ($V_{GS} = 10V$) $R_{DS(ON)} < 6m\Omega$ ($V_{GS} = 4.5V$)
<ul style="list-style-type: none"> - RoHS Compliant - Halogen Free 	100% UIS Tested! 100% R_g Tested!



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted			
Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ C$	20
		$T_C=70^\circ C$	17
Pulsed Drain Current ^C	I_{DM}	146	A
Avalanche Current ^C	I_{AR}	40	A
Repetitive avalanche energy $L=0.1mH$ ^C	E_{AR}	80	mJ
Power Dissipation ^B	P_D	$T_C=25^\circ C$	3.1
		$T_C=70^\circ C$	2
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics					
Parameter	Symbol	Typ	Max	Units	
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	31	40	$t \leq 10s$	
Maximum Junction-to-Ambient ^{A D}				Steady-State	
Maximum Junction-to-Lead	$R_{\theta JL}$	16	24	Steady-State $^\circ C/W$	

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30\text{V}$, $V_{GS}=0\text{V}$ $T_J=125^\circ\text{C}$			0.1 20	mA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			0.1	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1.2	1.8	2.2	V
$I_{D(ON)}$	On state drain current	$V_{GS}=10\text{V}$, $V_{DS}=5\text{V}$	146			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=20\text{A}$ $T_J=125^\circ\text{C}$		3.6 5.5	4.3 6.6	m Ω
		$V_{GS}=4.5\text{V}$, $I_D=18\text{A}$		4.8	6	m Ω
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=20\text{A}$		87		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.4	0.7	V
I_S	Maximum Body-Diode Continuous Current				6	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$	2975	3719	4463	pF
C_{oss}	Output Capacitance		485	693	900	pF
C_{rss}	Reverse Transfer Capacitance		204	340	476	pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$	0.28	0.56	0.84	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $I_D=20\text{A}$	48	60	72	nC
$Q_g(4.5\text{V})$	Total Gate Charge		20	25	30	nC
Q_{gs}	Gate Source Charge		12	15	18	nC
Q_{gd}	Gate Drain Charge		6	10	14	nC
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $R_L=0.75\Omega$, $R_{GEN}=3\Omega$		9.2		ns
t_r	Turn-On Rise Time			10.7		ns
$t_{D(off)}$	Turn-Off Delay Time			40		ns
t_f	Turn-Off Fall Time			12.5		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=20\text{A}$, $dI/dt=500\text{A}/\mu\text{s}$	10	13	16	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=20\text{A}$, $dI/dt=500\text{A}/\mu\text{s}$	21	26.5	32	nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on $T_{J(MAX)}=150^\circ\text{C}$, using $\leq 10\text{s}$ junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$.

D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using $<30\mu\text{s}$ pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}=150^\circ\text{C}$. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

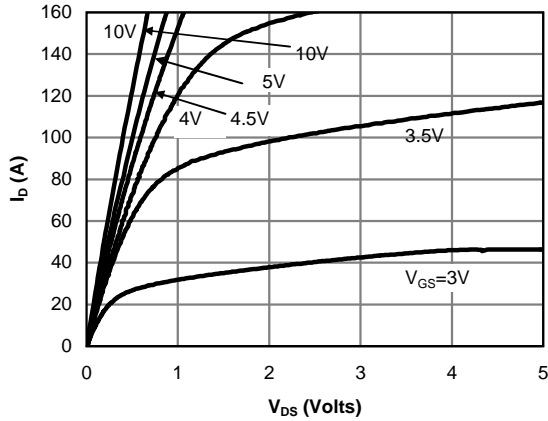


Fig 1: On-Region Characteristics (Note E)

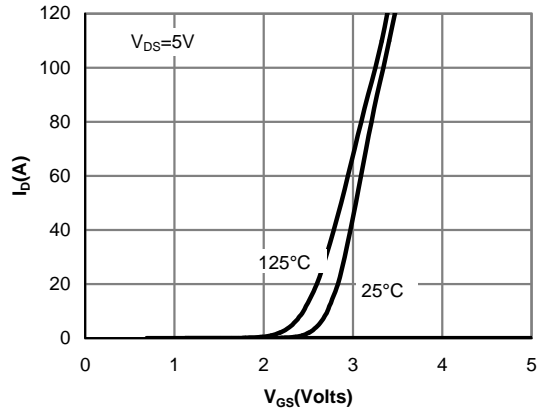


Figure 2: Transfer Characteristics (Note E)

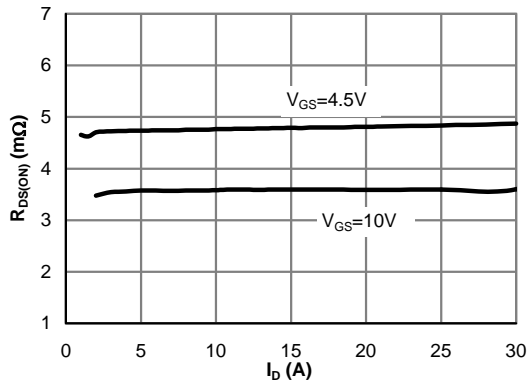


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

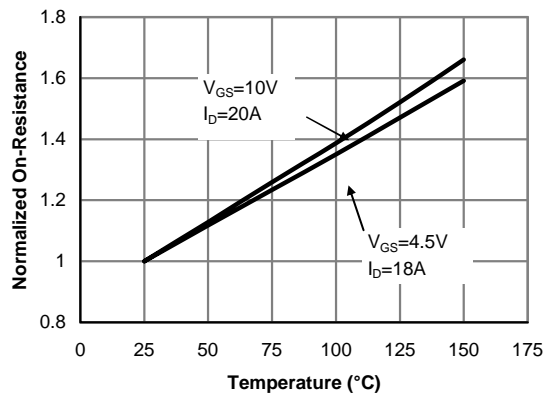


Figure 4: On-Resistance vs. Junction Temperature (Note E)

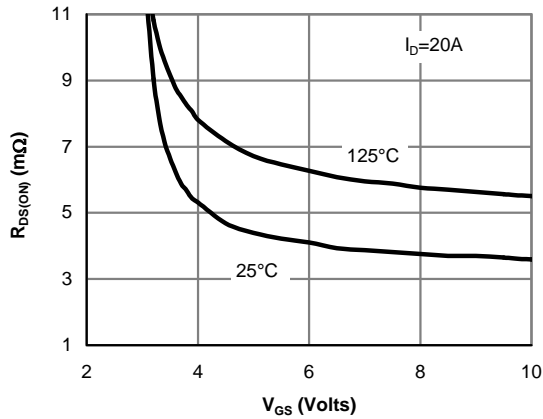


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

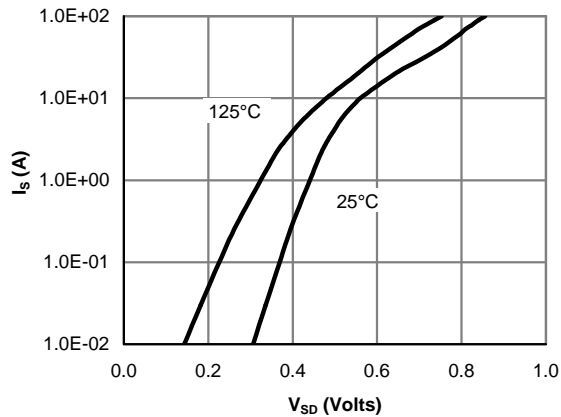


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

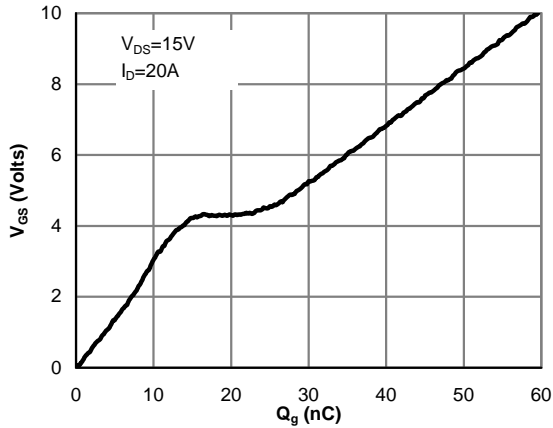


Figure 7: Gate-Charge Characteristics

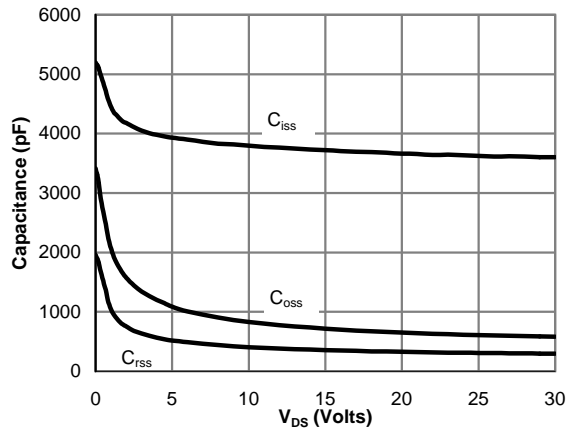


Figure 8: Capacitance Characteristics

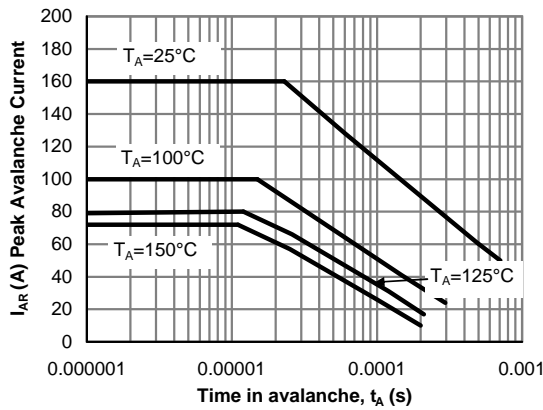


Figure 9: Single Pulse Avalanche capability (Note C)

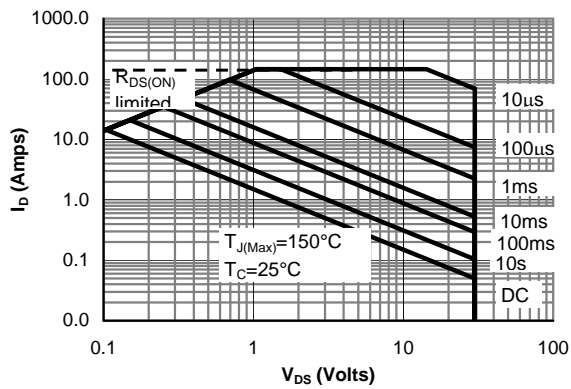


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

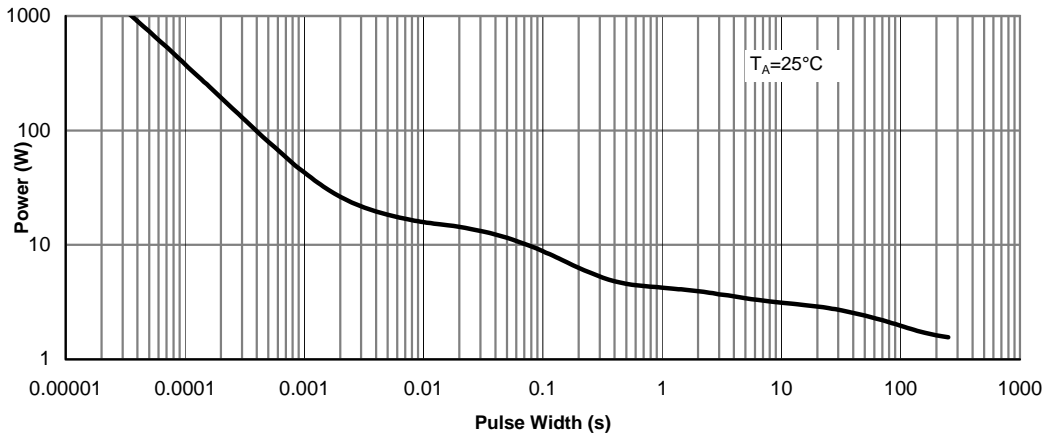


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

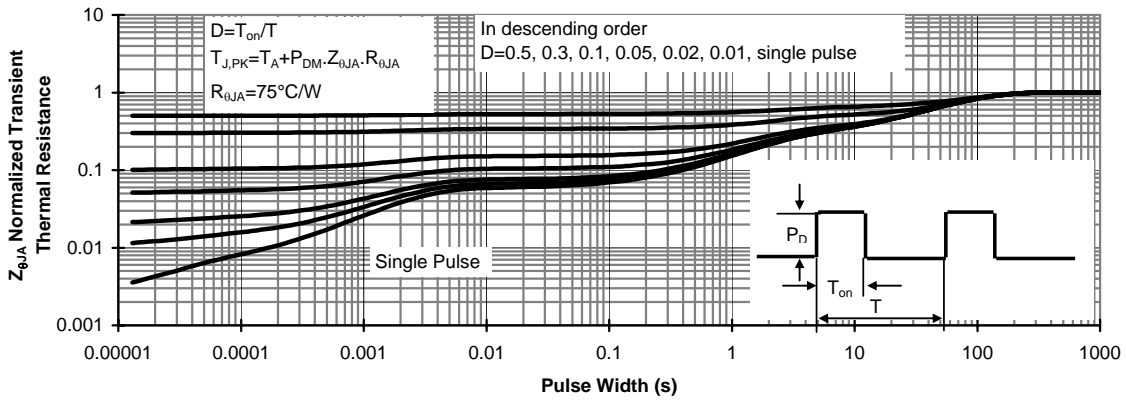


Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

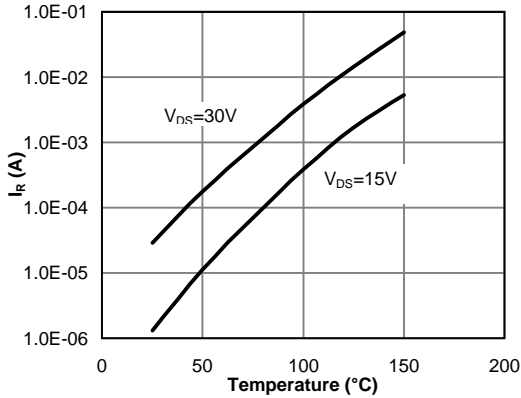


Figure 13: Diode Reverse Leakage Current vs. Junction Temperature

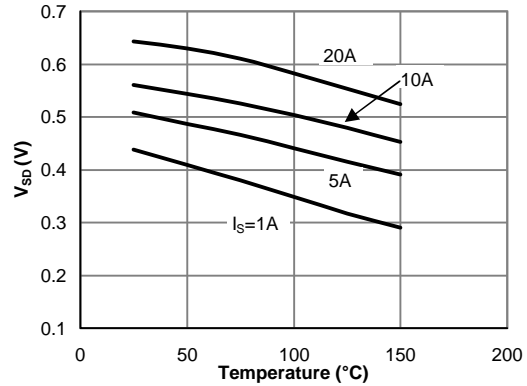


Figure 14: Diode Forward voltage vs. Junction Temperature

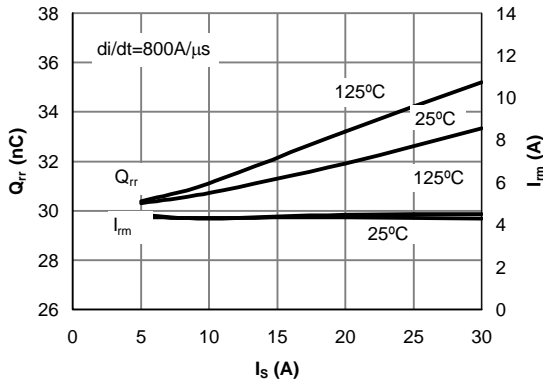


Figure 15: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current

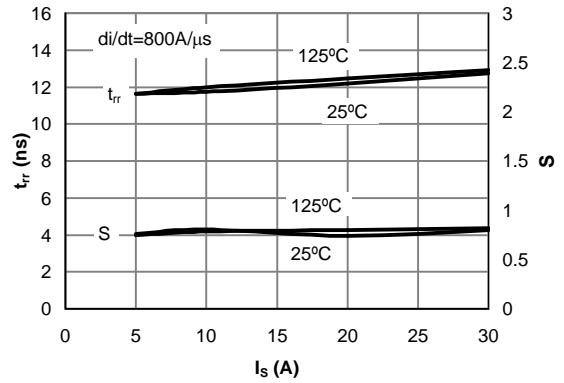


Figure 16: Diode Reverse Recovery Time and Softness Factor vs. Conduction Current

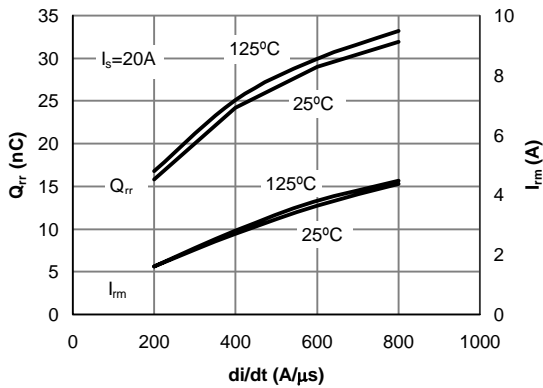


Figure 17: Diode Reverse Recovery Charge and Peak Current vs. di/dt

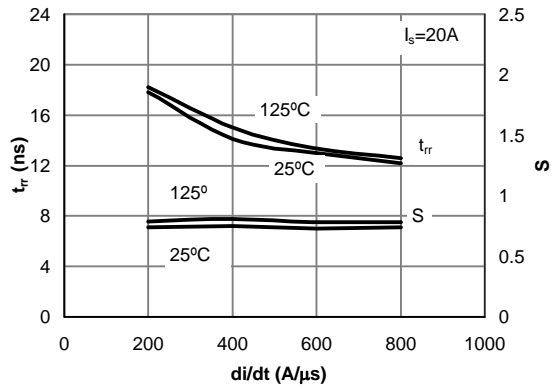
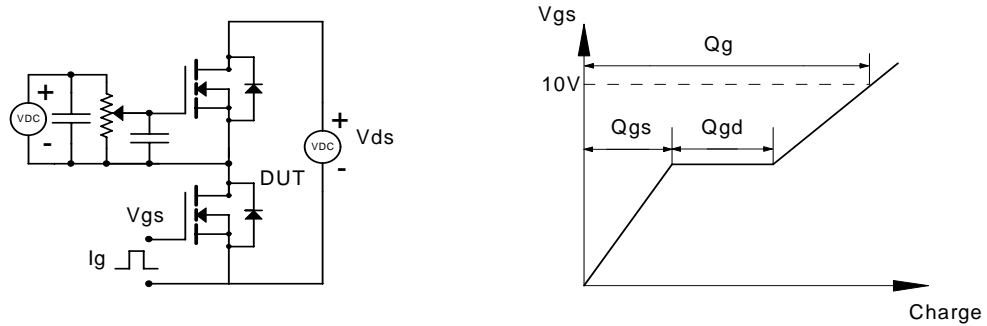
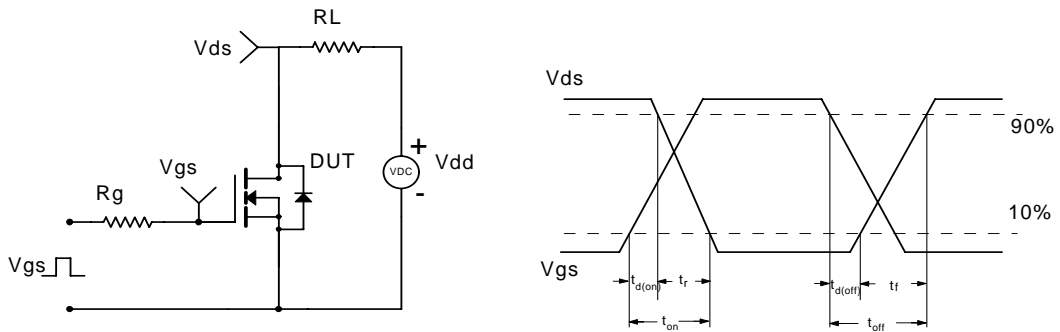


Figure 18: Diode Reverse Recovery Time and Softness Factor vs. di/dt

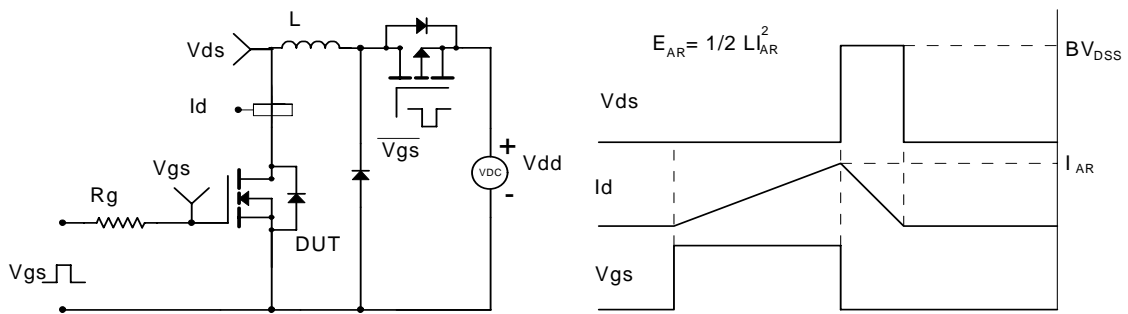
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

